

ABSTRACT OF THE DISCLOSURE

[0038] In one implementation, an opening within a capacitor electrode forming layer is formed over a substrate. A spacing layer is deposited over the capacitor electrode forming layer to within the opening over at least upper portions of sidewalls of the opening. The spacing layer is formed to be laterally thicker at an elevationally outer portion within the opening as compared to an elevationally inner portion within the opening. A spacer is formed within the opening by anisotropically etching the spacing layer. The spacer is laterally thicker at an elevationally outer portion within the opening as compared to an elevationally inner portion within the opening. After forming a first capacitor electrode layer laterally over the spacer, at least a portion of the spacer is removed and a capacitor dielectric region and a second capacitor electrode layer are formed over the first capacitor electrode layer.